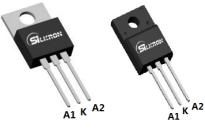
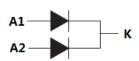


Main Product Characteristics:

IF	2×10A
VRRM	100V
Tj(max)	150 ℃
Vf(max)	0.8V





TO220 SSBD20100CT

TO220F SSBD20100CTF

Schematic Diagram

Features and Benefits:

- High Junction Temperature
- **High ESD Protection**
- High Forward & Reverse Surge capability



Description:

Schottky Barrier Rectifier designed for high frequency switch model power supplies such as adaptors and DC/DC convertors; this product special design for high forward and reverse surge capability

Absolute Rating:

Characterizes	Value	Unit				
Peak Repetitive Reverse Voltage	100	V				
RMS Reverse Voltage	70	V				
Average Ferward Current	Per diode	10	А			
Average Forward Current	Per device	20	А			
Non Repetitive Surge Forward Curre	180	А				
Peak Repetitive Reverse Surge Curre	0.5	А				
Maximum operation Junction Temper	-55~150	°C				
Storage Temperature Range	-55~150	°C				
	Characterizes Peak Repetitive Reverse Voltage RMS Reverse Voltage Average Forward Current Non Repetitive Surge Forward Curre Peak Repetitive Reverse Surge Curre Maximum operation Junction Temper	Characterizes Characterizes Peak Repetitive Reverse Voltage RMS Reverse Voltage Average Forward Current Per diode Per device Non Repetitive Surge Forward Current(tp=8.3ms sinusoidal) Peak Repetitive Reverse Surge Current(Tp=2us) Maximum operation Junction Temperature Range Maximum Range	$\begin{tabular}{ c c c c } \hline Characterizes & Value \\ \hline Characterizes & Value & 100 \\ \hline RMS Reverse Voltage & 70 \\ \hline RMS Reverse Voltage & 70 \\ \hline Average Forward Current & Per diode & 10 \\ \hline Per device & 20 \\ \hline Non Repetitive Surge Forward Current (tp=8.3ms sinusoidal) & 180 \\ \hline Peak Repetitive Reverse Surge Current (Tp=2us) & 0.5 \\ \hline Maximum operation Junction Temperature Range & -55~150 \\ \hline \end{tabular}$			

Thermal Resistance

Symbol	Characterizes	Value	Unit	
R _{θJC}	Maximum Thermal Resistance Junction To	2	°C/W	
$R_{ extsf{ heta}JC}$	Case(per leg)	TO220F	4	°C/W

Electrical Characterizes @T_A=25°C unless otherwise specified

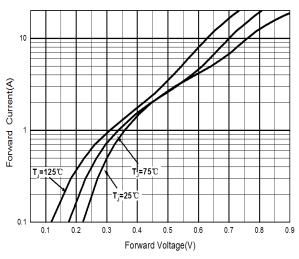
Symbol	Characterizes	Min	Тур	Max	Unit	Test Condition
V _R	Reverse Breakdown Voltage	100			V	I _R =0.5mA
V _F Forward Voltage Drop			0.8	V	I _F =10A, T _J =25℃	
			0.7		I _F =10A, T _J =125℃	
I _R	Leakage Current			0.1	mA	V _R =100V, T _J =25℃
				5		V _R =100V, T _J =125℃

©Silikron Semiconductor CO., LTD.

2013.4.23 www.silikron.com Version: 2.2 page



I-V Curves:



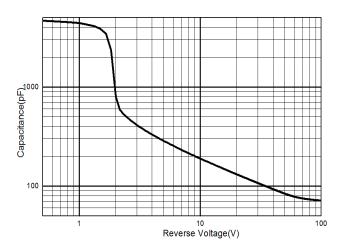


Figure 1: Typical Forward Characteristics

Figure 2: Typical Capacitance Characteristics

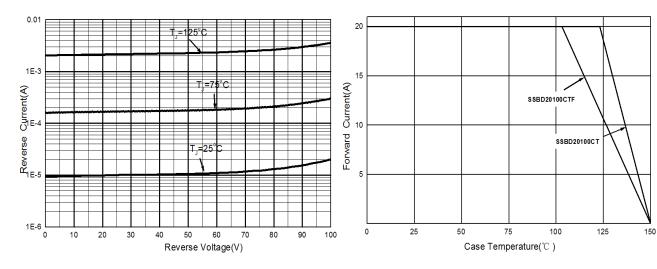
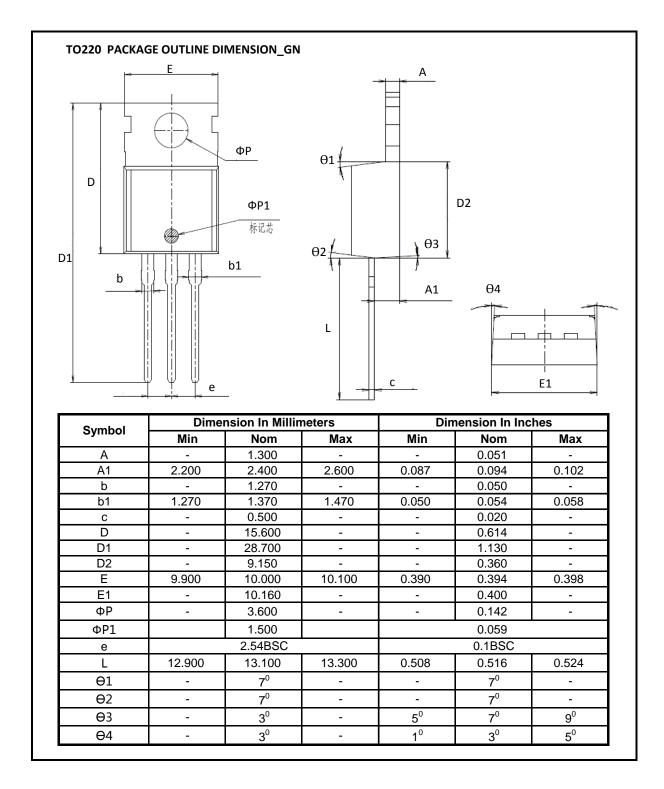


Figure 3: Typical Reverse Characteristics





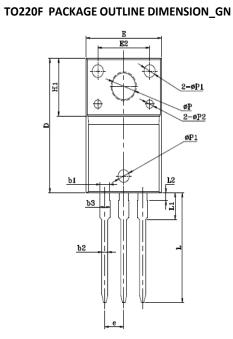
Mechanical Data:

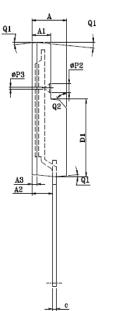




Q1

Q1





	ΨΨΨ 	<u>i</u>	-#-	<u>c</u>	E1	-
Dimension In Millimeters			Di	mension In Incl	sion In Inches	
Symbol	Min	Nom	Max	Min	Nom	Max
E	9.960	10.160	10.360	0.392	0.400	0.408
E1	9.840	10.040	10.240	0.387	0.395	0.403
E2	6.800	7.000	7.200	0.268	0.276	0.283
А	4.600	4.700	4.800	0.181	0.185	0.189
A1	2.440	2.540	2.640	0.096	0.100	0.104
A2	2.660	2.760	2.860	0.105	0.109	0.113
A3	0.600	0.700	0.800	0.024	0.028	0.031
С	-	0.500	-	-	0.020	-
D	15.780	15.870	15.980	0.621	0.625	0.629
D1	8.970	9.170	9.370	0.353	0.361	0.369
H1	6.500	6.700	6.800	0.256	0.264	0.268
е		2.54BSC	-		0.10BSC	-
ΦP	3.080	3.180	3.280	0.121	0.125	0.129
ΦΡ1	1.400	1.500	1.600	0.055	0.059	0.063
ΦΡ2	0.900	1.000	1.100	0.035	0.039	0.043
ΦP3	0.100	0.200	0.300	0.004	0.008	0.012
L	12.780	12.980	13.180	0.503	0.511	0.519
L1	2.970	3.170	3.370	0.117	0.125	0.133
L2	0.830	0.930	1.030	0.033	0.037	0.041
Q1	3°	5°	7°	3°	5°	7°
Q2	43°	45°	47°	43°	45°	47°
b1	1.180	1.280	1.380	0.046	0.050	0.054
b2	0.760	0.800	0.840	0.030	0.031	0.033
b3	-	-	1.420	-	-	0.056



Ordering and Marking Information

Device Marking: SSBD200100CT&SSBD20100CTF

Package (Available) TO-220&TO220F Operating Temperature Range C : -55 to 150 °C

Devices per Unit

Package Type	Units/ Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Car ton Box
TO220	50	20	1000	6	6000
TO220F	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High	Tj=125℃ to 150℃ @	168 hours	3 lots x 77 devices
Temperature	80% of Max	500 hours	
Reverse	VDSS/VCES/VR	1000 hours	
Bias(HTRB)			





ATTENTION:

- Any and all Silikron products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Silikron representative nearest you before using any Silikron products described or contained herein in such applications.
- Silikron assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Silikron products described or contained herein.
- Specifications of any and all Silikron products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- Silikron Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all Silikron products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Silikron Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Silikron believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to
 product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the
 Silikron product that you intend to use.
- This catalog provides information as of Dec, 2008. Specifications and information herein are subject to change without notice.

Customer Service

Worldwide Sales and Service: Sales@silikron.com Technical Support: Technical@silikron.com Suzhou Silikron Semiconductor Corp. 11A, 428 Xinglong Street, Suzhou Industrial Park, P.R.China TEL: (86-512) 62560688 FAX: (86-512) 65160705 E-mail: Sales@silikron.com